XN0F261

Silicon NPN epitaxial planar type

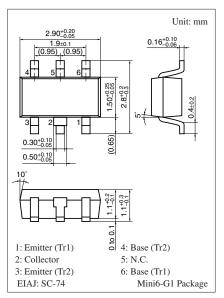
For muting

■ Features

- Two elements incorporated into one package (Collector-coupled transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

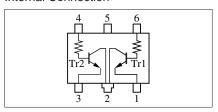
■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	30	V	
Collector-emitter voltage (Base open)	V _{CEO}	20	V	
Emitter-base voltage (Collector open)	V _{EBO}	5	V	
Collector current	I_C	600	mA	
Total power dissipation	P_{T}	300	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



Marking Symbol: 6B

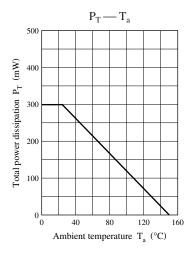
Internal Connection

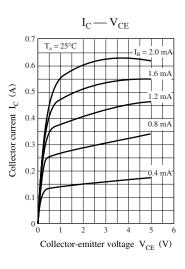


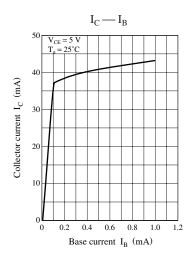
\blacksquare Electrical Characteristics $~T_a = 25^{\circ}C \pm 3^{\circ}C$

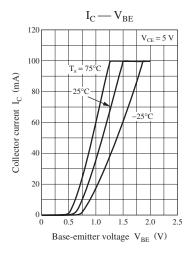
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 1 \mu A, I_E = 0$	30			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 1 \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 30 \text{ V}, I_{E} = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			1	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 50 \text{ mA}$	100		600	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$			80	mV
Input resistance	R_1		-30%	3.3	+30%	kΩ
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

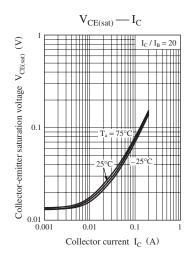
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

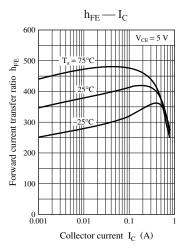












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